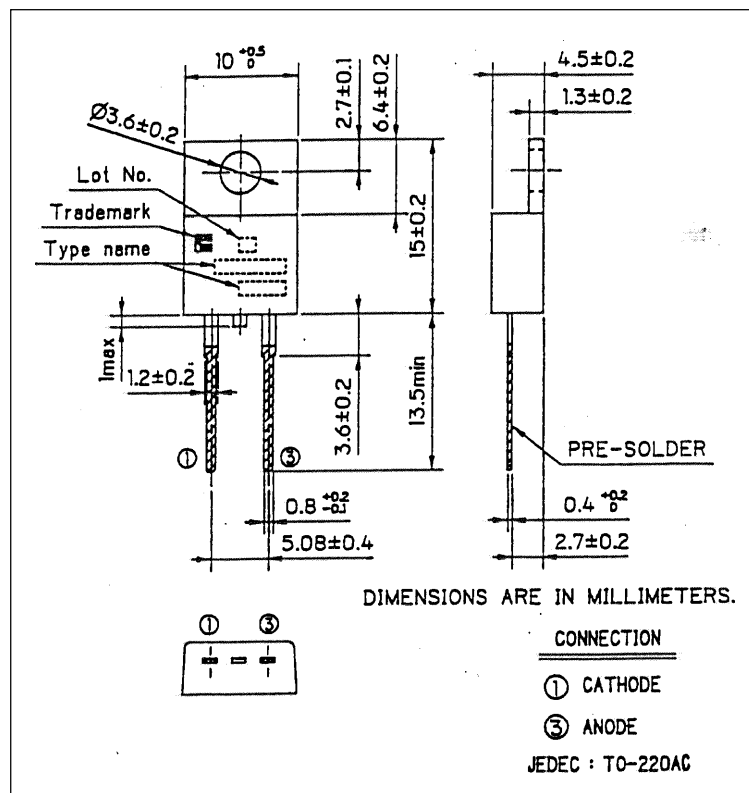
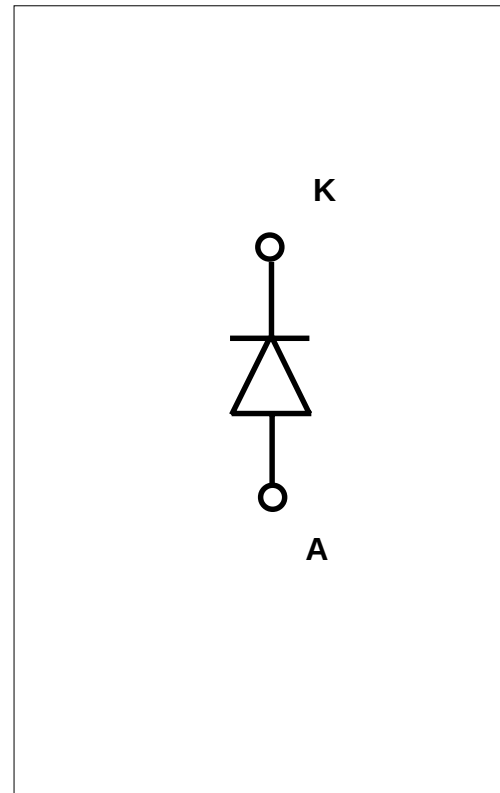


Fast Recovery Diode for IGBT

Outline Drawings Units mm



Equivalent circuit



Maximum ratings and characteristics

Absolute maximum ratings (Tc=25°C)

Item	Symbol	Test Conditions		Ratings	Units
Repetitive Reverse Voltage	V _{RRM}			600	V
Repetitive peak surge current	I _{FM}	20kHz Duty 50% Squ. wave	Tc=100°C	10	A
			Tc=25°C	19	A
Average rectified forward current	I _{F(A)}	DC		10	A
Non-repetitive peak surge current	I _{FSM}	Pulse 10ms, sin. wave		63	A
Maximam Power Dissipaion	P _o			35	W
Operating Temperature	T _j			+150	°C
Storage Temperature	T _{stg}			-40 to +150	°C
Mounting Screw Torque				50	N·cm

Electrical characteristics (at Tc=25°C unless otherwise specified)

Item	Symbol	Test Conditions	Max	Units
Reverse Current	I _R	V _R = 600V	1.0	mA
Forward voltage	V _{FM}	I _F = 10A	3.0	V
Reverse recovery time	t _{rr}	I _F = 10A, V _R =200V, di/dt=100A/μs	0.3	μs

Thermal resistance characteristics

Item	Symbol	Test Conditions	Max	Units
Thermal resistance	R _{th(j-c)}	junction to case	3.57	°C/W

■ Characteristics

